

AMENDMENTS TO THE CLAIMS

1. (Cancelled)

2. (Cancelled)

3. (Cancelled)

4. (New) A method of manufacturing a semiconductor device, comprising the steps of:

forming a stopper film on a main surface of a semiconductor substrate;

forming a trench at the main surface of said semiconductor substrate using said stopper film as a mask;

forming an insulating film to fill said trench and to reach a level higher than said main surface and lower than an upper surface of said stopper film;

depositing a silicon nitride film to cover a bottom surface of a recess that is formed of a side surface of said stopper film and an upper surface of said insulating film;

forming an oxide-type film on said silicon nitride film covering the bottom surface of said recess; and

removing said stopper film using said oxide-type film as a mask.